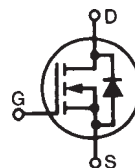


PolarHV™ HiPerFET Power MOSFET

N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Diode

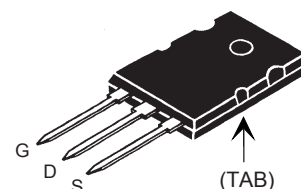
IXFK 48N60P
IXFX 48N60P

$V_{DSS} = 600 \text{ V}$
 $I_{D2} = 48 \text{ A}$
 $R_{DS(on)} \leq 135 \text{ m}\Omega$
 $t_{rr} \leq 200 \text{ ns}$

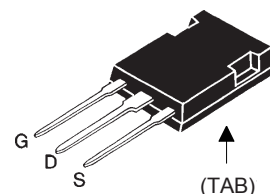


Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ \text{C to } 150^\circ \text{C}$	600	V
V_{DGR}	$T_J = 25^\circ \text{C to } 150^\circ \text{C}; R_{GS} = 1 \text{ M}\Omega$	600	V
V_{GSS}	Continuous	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	$T_C = 25^\circ \text{C}$	48	A
I_{DM}	$T_C = 25^\circ \text{C}$, pulse width limited by T_{JM}	110	A
I_{AR}	$T_C = 25^\circ \text{C}$	48	A
E_{AR}	$T_C = 25^\circ \text{C}$	70	mJ
E_{AS}	$T_C = 25^\circ \text{C}$	2.0	J
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100 \text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ \text{C}$, $R_G = 4 \Omega$	20	V/ns
P_D	$T_C = 25^\circ \text{C}$	830	W
T_J		-55 ... +150	$^\circ \text{C}$
T_{JM}		150	$^\circ \text{C}$
T_{stg}		-55 ... +150	$^\circ \text{C}$
M_d	Mounting torque (TO-264)	1.13/10 Nm/lb.in.	
Weight	TO-264	10	g
	PLUS247	6	g
T_L	1.6 mm (0.062 in.) from case for 10 s	300	$^\circ \text{C}$
T_{SOLD}	Plastic body for 10 s	260	$^\circ \text{C}$

TO-264 (IXFK)



PLUS247 (IXFX)



G = Gate D = Drain
S = Source Tab = Drain

Features

- International standard packages
- Fast recovery diode
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
- easy to drive and to protect

Advantages

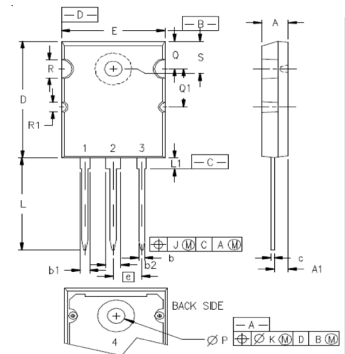
- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions ($T_J = 25^\circ \text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0 \text{ V}$, $I_D = 250 \mu\text{A}$	600		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 8 \text{ mA}$	3.0		5.0 V
I_{GSS}	$V_{GS} = \pm 30 \text{ V}_{DC}$, $V_{DS} = 0$			$\pm 200 \text{ nA}$
I_{DSS}	$V_{DS} = V_{DSS}$			25 μA
	$V_{GS} = 0 \text{ V}$ $T_J = 125^\circ \text{C}$			1000 μA
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$, $I_D = 0.5 I_{D25}$ Pulse test, $t \leq 300 \mu\text{s}$, duty cycle $d \leq 2 \%$			135 m Ω

Symbol	Test Conditions	Characteristic Values		
		(T _J = 25° C, unless otherwise specified)		
		Min.	Typ.	Max.
g_{fs}	V _{DS} = 20 V; I _D = 0.5 I _{D25} , pulse test	35	53	S
C_{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz		8860	pF
C_{oss}			850	pF
C_{rss}			60	pF
t_{d(on)}	V _{GS} = 10 V, V _{DS} = 0.5 I _{D25} R _G = 2 Ω (External)		30	ns
t_r			25	ns
t_{d(off)}			85	ns
t_f			22	ns
Q_{g(on)}	V _{GS} = 10 V, V _{DS} = 0.5 V _{DSS} , I _D = 0.5 I _{D25}		150	nC
Q_{gs}			50	nC
Q_{gd}			50	nC
R_{thJC}	TO-264 and PLUS247		0.15	° C/W
R_{thCs}				° C/W

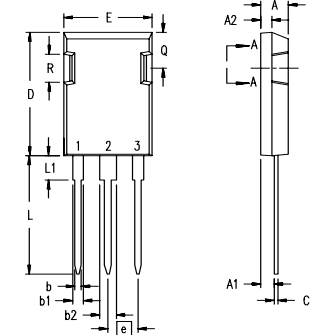
Source-Drain Diode

Symbol	Test Conditions	Characteristic Values		
		(T _J = 25° C, unless otherwise specified)		
		Min.	Typ.	Max.
I_S	V _{GS} = 0 V			48 A
I_{SM}	Repetitive			110 A
V_{SD}	I _F = I _S , V _{GS} = 0 V, Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %			1.5 V
t_{rr}	I _F = 25A, -di/dt = 100 A/μs V _R = 100V		0.8	200 ns
Q_{RM}				μC
I_{RM}				A

TO-264 (IXFK) Outline


- 1 - GATE
2, 4 - DRAIN (COLLECTOR)
3 - SOURCE (EMITTER)

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.209	4.70	5.31
A1	.102	.118	2.59	3.00
b	.037	.055	0.94	1.40
b1	.087	.102	2.21	2.59
b2	.110	.126	2.79	3.20
c	.017	.029	0.43	0.74
D	1.007	1.047	25.58	26.59
E	.760	.799	19.30	20.29
e	.215 BSC		5.46 BSC	
J	.000	.010	0.00	0.25
K	.000	.010	0.00	0.25
L	.779	.842	19.79	21.39
L1	.087	.102	2.21	2.59
ØP	.122	.138	3.10	3.51
Q	.240	.256	6.10	6.50
Q1	.330	.346	8.38	8.79
ØR	.155	.187	3.94	4.75
ØR1	.085	.093	2.16	2.36
S	.243	.253	6.17	6.43

PLUS 247™ (IXFX) Outline


- Terminals: 1 - Gate
2 - Drain (Collector)
3 - Source (Emitter)
4 - Drain (Collector)

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A ₁	2.29	2.54	.090	.100
A ₂	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b ₁	1.91	2.13	.075	.084
b ₂	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	0.244
R	4.32	4.83	.170	.190

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585
4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2

www.DataSheet4U.com

Fig. 1. Output Characteristics
@ 25°C

www.DataSheet4U.com

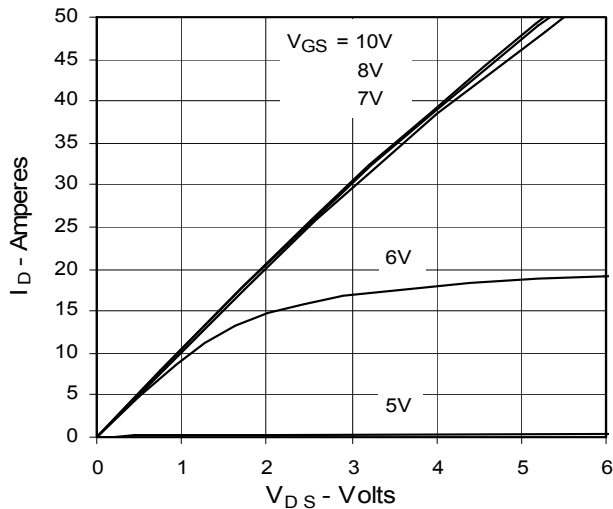


Fig. 2. Extended Output Characteristics
@ 25°C

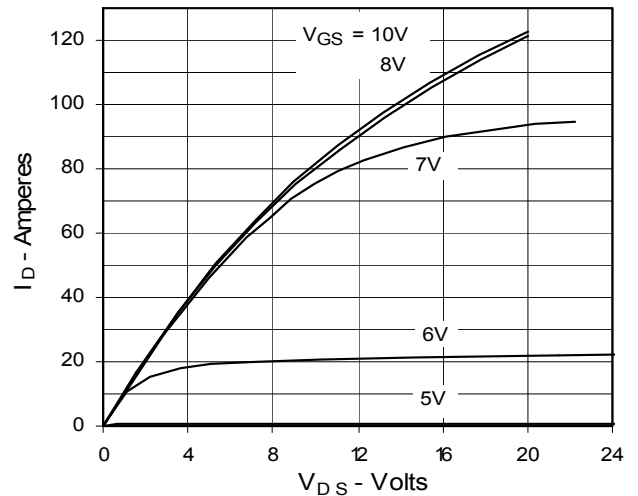


Fig. 3. Output Characteristics
@ 125°C

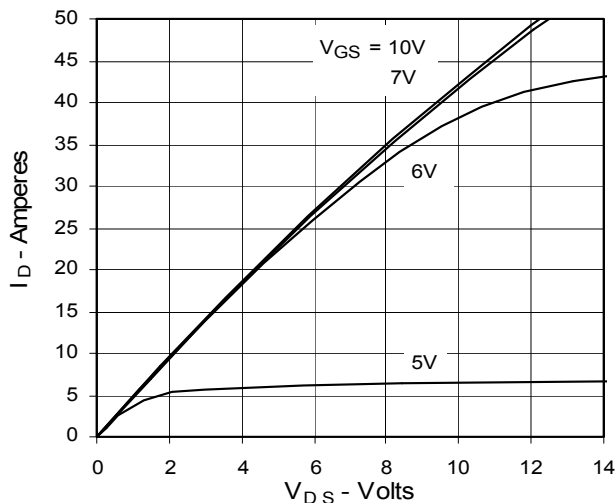


Fig. 4. $R_{DS(on)}$ Normalized to 0.5 I_{D25} Value vs. Junction Temperature

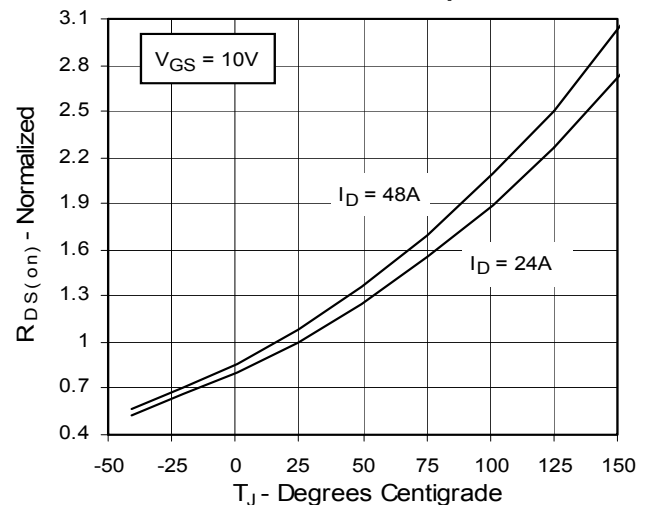


Fig. 5. $R_{DS(on)}$ Normalized to 0.5 I_{D25} Value vs. I_D

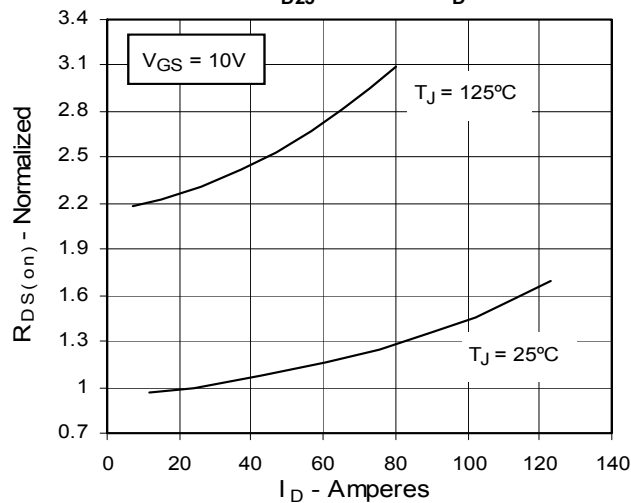


Fig. 6. Drain Current vs. Case Temperature

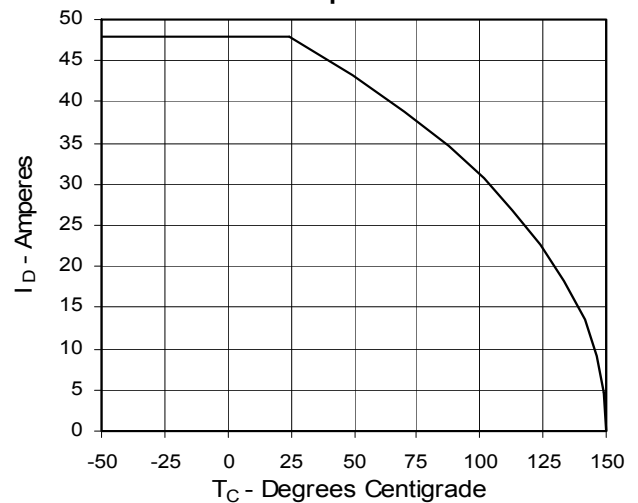
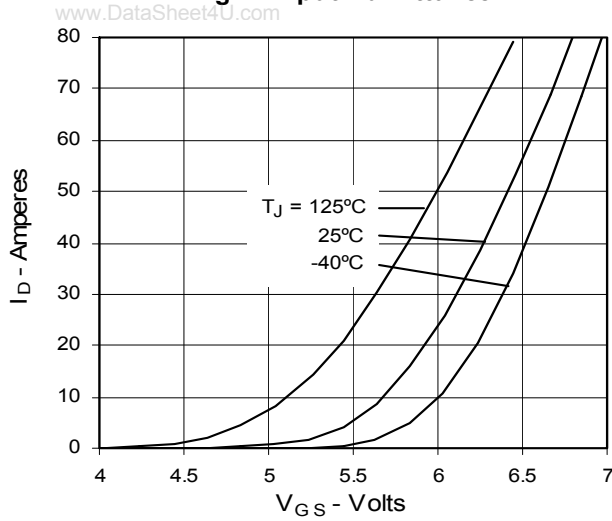
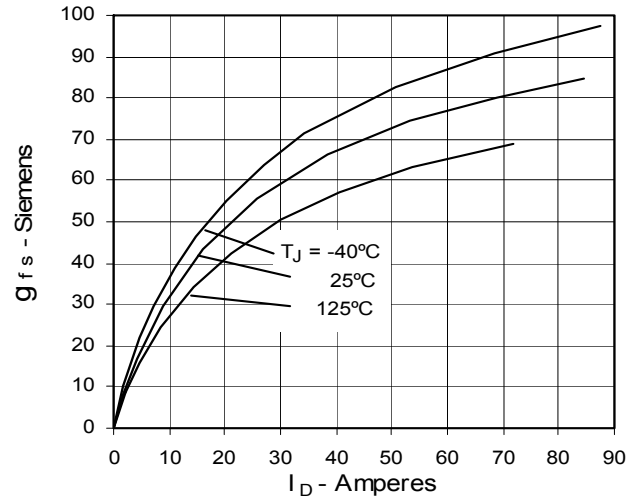
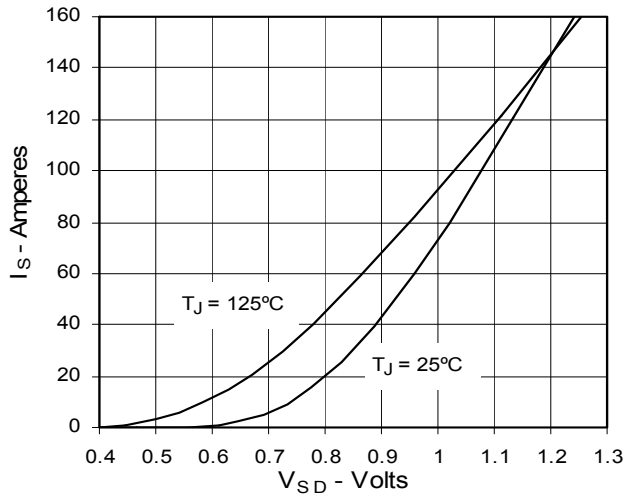
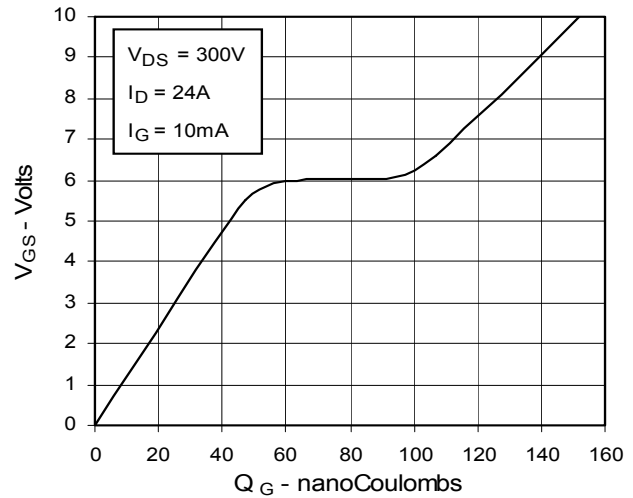
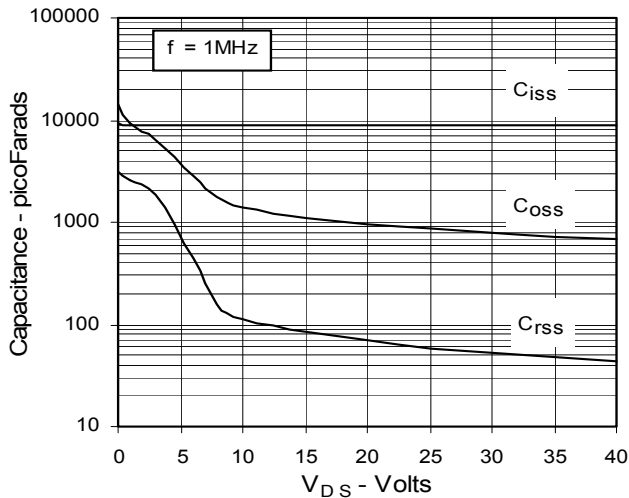


Fig. 7. Input Admittance

Fig. 8. Transconductance

Fig. 9. Source Current vs. Source-To-Drain Voltage

Fig. 10. Gate Charge

Fig. 11. Capacitance

Fig. 13. Maximum Transient Thermal Resistance
